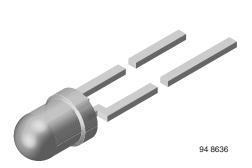
VSLY3850

www.vishay.com

Vishay Semiconductors

High Speed Infrared Emitting Diode, 850 nm, Surface Emitter Technology



As part of the SurfLight[™] portfolio, the VSLY3850 is an infrared, 850 nm emitting diode based on GaAlAs surface

emitter chip technology with extreme high radiant intensity,

high optical power and high speed, molded in a clear,

FEATURES

- Package type: leaded
- Package form: T-1, clear epoxy
- Dimensions: Ø 3 mm
- Peak wavelength: $\lambda_p = 850 \text{ nm}$
- High speed
- High radiant power
- · High radiant intensity
- Angle of half intensity: $\phi = \pm 18^{\circ}$
- · Suitable for high pulse current operation
- · Good spectral matching with CMOS cameras
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Infrared radiation source for operation with CMOS cameras
- High speed IR data transmission
- 3D TV application
- Light curtains

PRODUCT SUMMARY COMPONENT l_e (mW/sr) φ (deg) λ_p (nm) t_r (ns) VSLY3850 70 ± 18 850 10

Note

DESCRIPTION

untinted T1 plastic package.

Test conditions see table "Basic Characteristics"

| ORDERING INFORMATION | | | | | | | |
|----------------------|-----------|-------------------------------|--------------|--|--|--|--|
| ORDERING CODE | PACKAGING | REMARKS | PACKAGE FORM | | | | |
| VSLY3850 | Bulk | MOQ: 5000 pcs, 5000 pcs/bulk | T-1 | | | | |
| VSLY3850-ASZ | Ammopack | MOQ: 10 000 pcs, 2000 pcs/box | T-1 | | | | |

Note

MOQ: minimum order quantity

| ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified) | | | | | | |
|--|--|-------------------|-------------|------|--|--|
| PARAMETER | TEST CONDITION | SYMBOL | VALUE | UNIT | | |
| Reverse voltage | | V _R | 5 | V | | |
| Forward current | | I _F | 100 | mA | | |
| Peak forward current | $t_p/T = 0.5, t_p = 100 \ \mu s$ | I _{FM} | 200 | mA | | |
| Surge forward current | t _p = 100 μs | I _{FSM} | 1 | A | | |
| Power dissipation | | Pv | 190 | mW | | |
| Junction temperature | | Tj | 100 | °C | | |
| Operating temperature range | | T _{amb} | -40 to +85 | °C | | |
| Storage temperature range | | T _{stg} | -40 to +100 | °C | | |
| Soldering temperature | $t \leq 5 \text{ s}, 2 \text{ mm}$ from case | T _{sd} | 260 | °C | | |
| Thermal resistance junction / ambient | J-STD-051, leads 7 mm, soldered on PCB | R _{thJA} | 300 | K/W | | |

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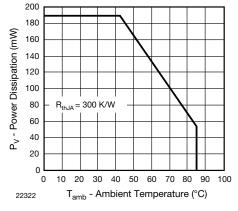


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

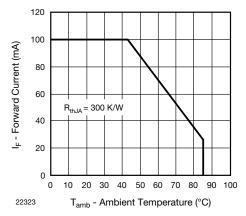


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified) | | | | | | | | |
|---|--|------------------|------------------------------------|-------|------|-------|--|--|
| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT | | |
| Forward voltage | l _F = 100 mA, t _p = 20 ms | V _F | - | 1.65 | 1.9 | V | | |
| | I _F = 1 A, t _p = 100 μs | V _F | - | 2.9 | - | V | | |
| Temperature coefficient of V _F | I _F = 1 mA | TK _{VF} | - | -1.45 | - | mV/K | | |
| | I _F = 10 mA | TK _{VF} | - | -1.25 | - | mV/K | | |
| Reverse current | | I _R | Not designed for reverse operation | | | μA | | |
| Junction capacitance | $V_R = 0 V$, f = 1 MHz, E = 0 mW/cm ² | CJ | - | 125 | - | pF | | |
| Radiant intensity | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$ | l _e | 35 | 70 | 105 | mW/sr | | |
| | I _F = 1 A, t _p = 100 μs | l _e | - | 600 | - | mW/sr | | |
| Radiant power | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$ | фе | - | 55 | - | mW | | |
| Temperature coefficient of radiant power | I _F = 1 mA | TK_{\phie} | - | -0.35 | - | %/K | | |
| Angle of half intensity | | φ | - | ± 18 | - | deg | | |
| Peak wavelength | I _F = 30 mA | λρ | 840 | 850 | 870 | nm | | |
| Spectral bandwidth | I _F = 30 mA | Δλ | - | 30 | - | nm | | |
| Temperature coefficient of Ip | I _F = 30 mA | TK _{λp} | - | 0.25 | - | nm | | |
| Rise time | $I_F = 100 \text{ mA}, 20 \% \text{ to } 80 \%$ | t _r | - | 10 | - | ns | | |
| Fall time | $I_F = 100 \text{ mA}, 20 \% \text{ to } 80 \%$ | t _f | - | 10 | - | ns | | |



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BASIC CHARACTERISTICS (Tamb = 25 °C, unless otherwise specified)

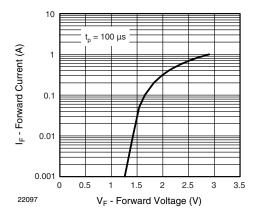


Fig. 3 - Forward Current vs. Forward Voltage

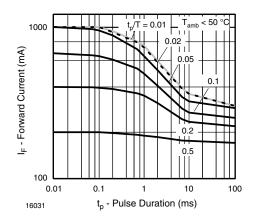


Fig. 4 - Pulse Forward Current vs. Pulse Duration

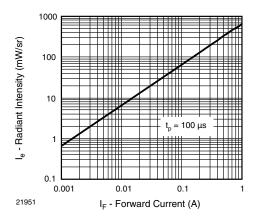


Fig. 5 - Radiant Intensity vs. Forward Current

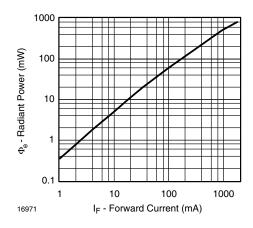


Fig. 6 - Radiant Power vs. Forward Current

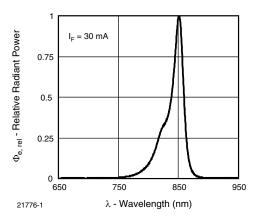


Fig. 7 - Relative Radiant Power vs. Wavelength

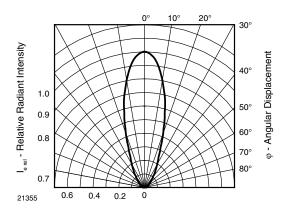


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

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For technical questions, contact: emittertechsupport@vishay.com

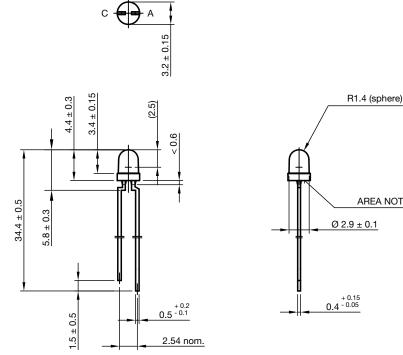
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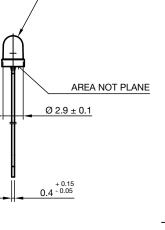
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PACKAGE DIMENSIONS in millimeters







technical drawings according to DIN specifications

Drawing-No.: 6.544-5264.01-4 Issue: 4; 28.07.14



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